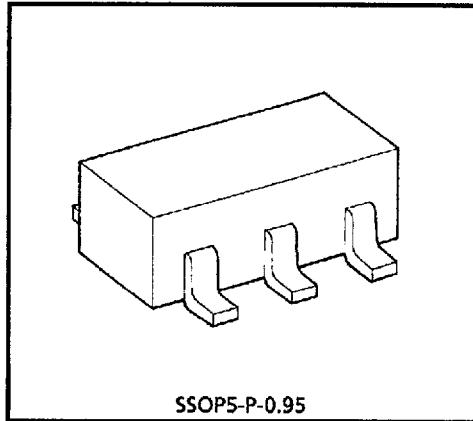


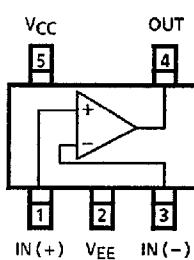
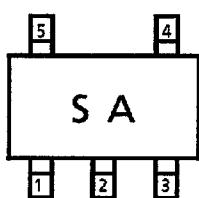
TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA75S01F**SINGLE OPERATIONAL AMPLIFIER****FEATURES**

- In the linear mode the input common mode voltage range includes ground.
- The internally compensated Operational Amplifier is small package.
- Low power dissipation and power drain suitable for battery operation.
- Differential input voltage range equal to the power supply voltage.
- Large output voltage swing : 0V_{DC} to 3.4V_{DC} ($V_{DC} = 5V_{DC}$)
- Wide power supply voltage range and single power supply is possible.
- Single supply 3V_{DC} to 12V_{DC} or dual supplies $\pm 1.5V_{DC}$ to $\pm 6V_{DC}$.



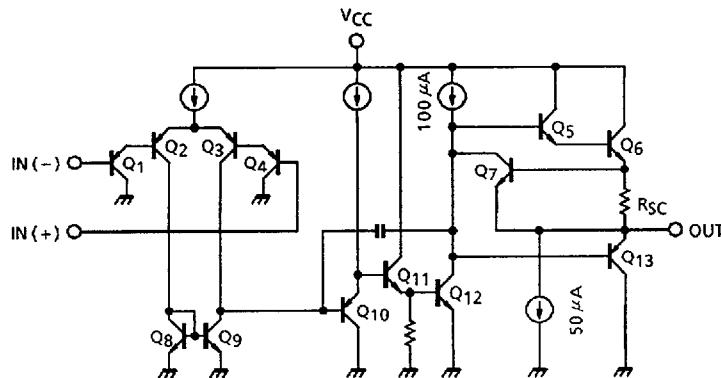
Weight : 0.014g (Typ.)

MARKING (TOP VIEW)**PIN CONNECTION (TOP VIEW)**

961001EBA2

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- The information contained herein is subject to change without notice.

EQUIVALENT CIRCUIT

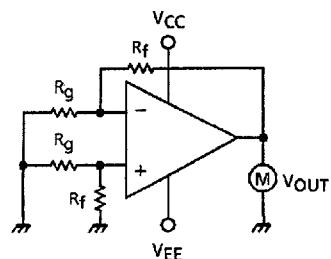
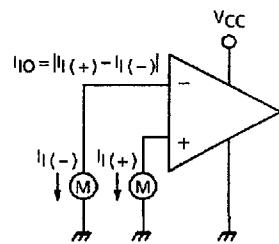
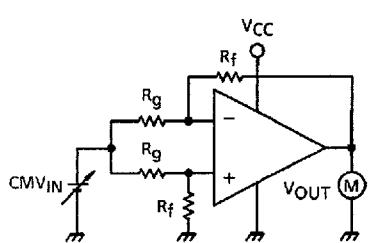
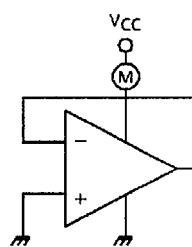
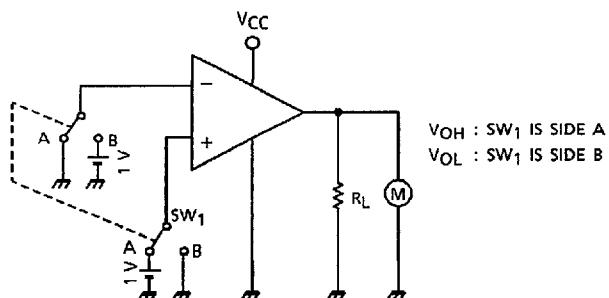
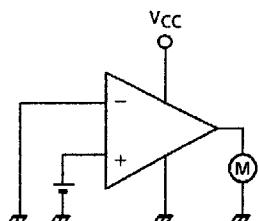
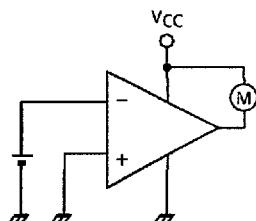
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

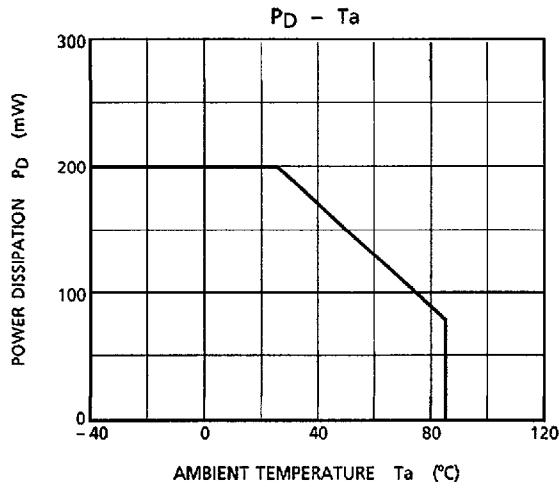
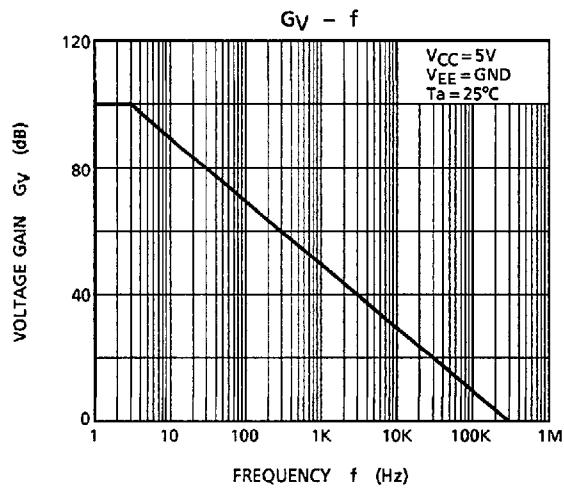
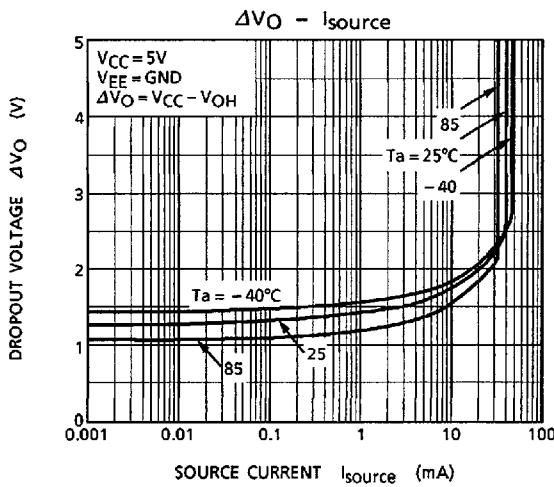
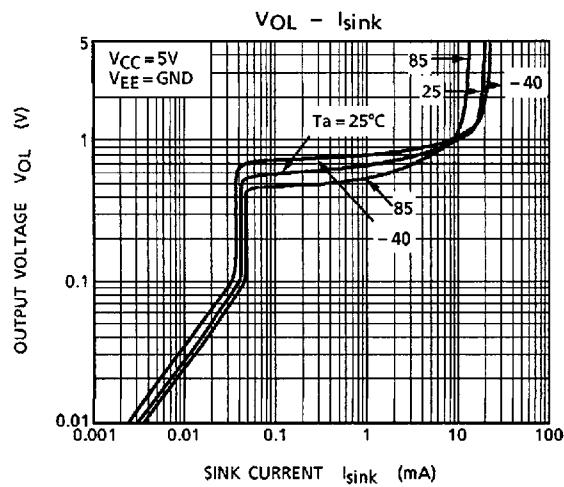
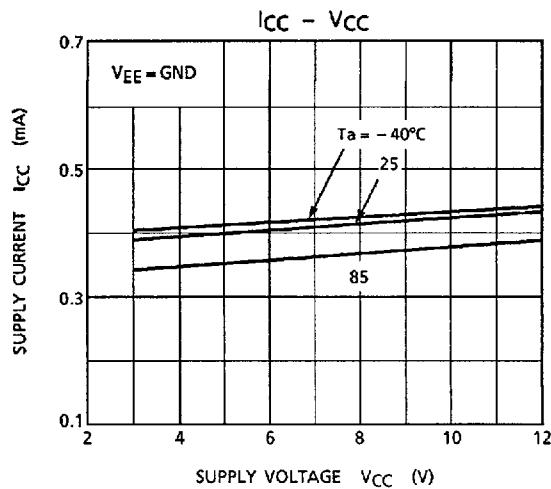
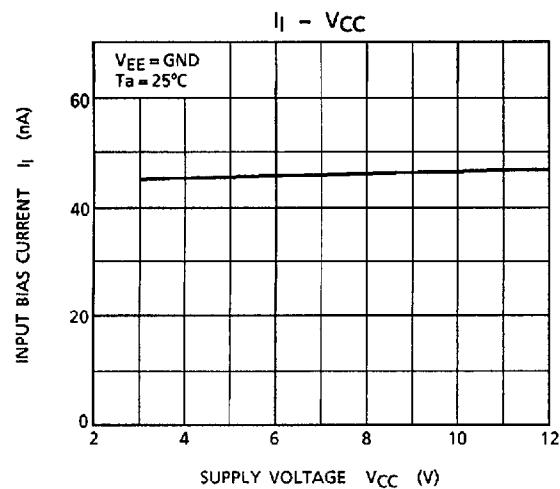
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}, V_{EE}	$\pm 6 \text{ or } 12$	V
Differential Input Voltage	DV_{IN}	± 12	V
Input Voltage	V_{IN}	$-0.3 \sim V_{CC}$	V
Power Dissipation	P_D	200	mW
Operating Temperature	T_{opr}	$-40 \sim 85$	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \sim 125$	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($V_{CC} = 5\text{V}$, $V_{EE} = \text{GND}$, $T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	V_{IO}	1	$R_g \leq 10\text{k}\Omega$	—	2	7	mV
Input Offset Current	I_{IO}	2	—	—	5	50	nA
Input Bias Current	I_I	2	—	—	45	250	nA
Common Mode Input Voltage	CMV_{IN}	3	—	0	—	$V_{CC} - 1.5$	V
Supply Current	I_{CC}	4	—	—	0.4	0.8	mA
Voltage Gain	G_V	—	$R_L \geq 2\text{k}\Omega$	86	100	—	dB
Maximum Output Voltage Swing	V_{op-p}	5	$R_L = 2\text{k}\Omega$	0	—	3.4	V
Common Mode Rejection Ratio	$CMRR$	3	—	65	85	—	dB
Supply Voltage Rejection Ratio	$SVRR$	—	$R_g = 10\text{k}\Omega$	65	100	—	dB
Source Current	I_{source}	6	$IN(-) = 0\text{V}$, $IN(+) = 1\text{V}$	20	40	—	mA
Sink Current	I_{sink}	7	$IN(-) = 1\text{V}$, $IN(+) = 0\text{V}$	10	20	—	mA
Unity Gain Cross Frequency	f_T	—	—	—	0.3	—	MHz

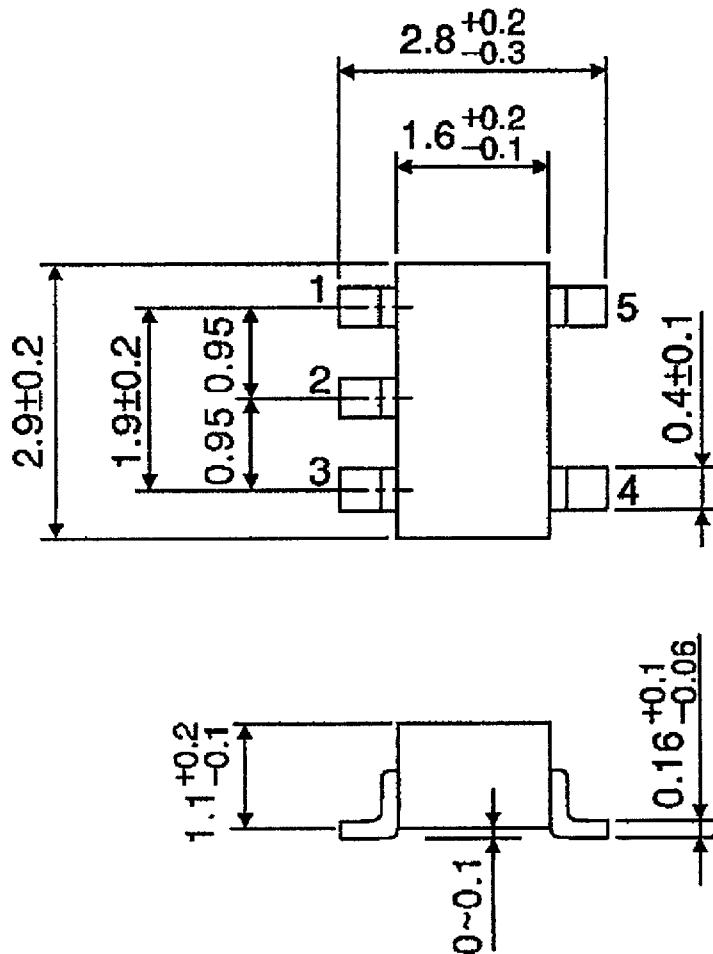
TEST CIRCUIT

(1) V_{IO} (2) I_I , I_{IO} (3) CMV_{IN}, CMRR(4) I_{CC} (5) V_{op-p} (6) I_{source} (7) I_{sink} 



OUTLINE DRAWING
SSOP5-P-0.95

Unit : mm



Weight : 0.014g (Typ.)